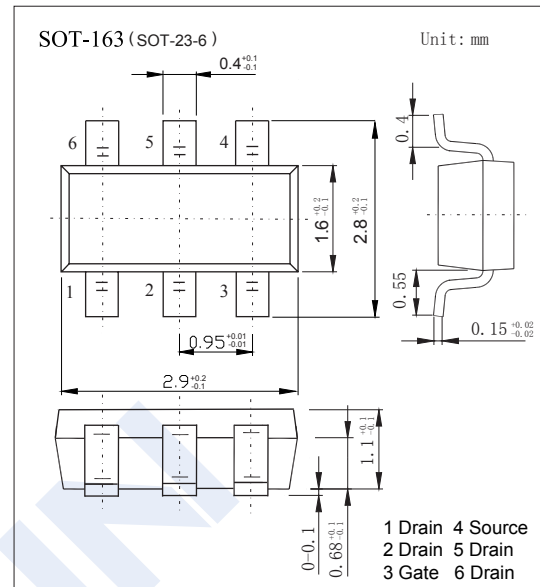
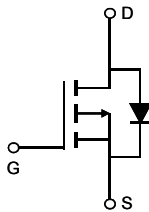


P-Channel MOSFET

AO6405 (KO6405)

■ Features

- $V_{DS} (V) = -30V$
- $I_D = -5 A$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 52m\Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 87m\Omega$ ($V_{GS} = -4.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current	T _A =25°C	I _D	-5	A
	T _A =70°C		-4.2	
Pulsed Drain Current		I _{DM}	-20	
Power Dissipation	T _A =25°C	P _D	2	W
	T _A =70°C		1.3	
Thermal Resistance.Junction- to-Ambient	t ≤ 10s	R _{thJA}	62.5	°C/W
	Steady-State		110	
Thermal Resistance.Junction- to-Lead		R _{thJL}	50	
Junction Temperature		T _J	150	°C
Junction Storage Temperature Range		T _{stg}	-55 to 150	

P-Channel MOSFET

AO6405 (KO6405)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250 μA, V _{GS} =0V	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
		V _{DS} =-30V, V _{GS} =0V, T _J =55°C			-5	
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250 μA	-1.4		-2.4	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-5A			52	mΩ
		V _{GS} =-10V, I _D =-5A, T _J =125°C			70	
		V _{GS} =-4.5V, I _D =-4A			87	
On state drain current	I _{D(ON)}	V _{GS} =-10V, V _{DS} =-5V	-20			A
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-5A		10		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-15V, f=1MHz		520		pF
Output Capacitance	C _{oss}			100		
Reverse Transfer Capacitance	C _{rss}			65		
Gate resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	3.5		11.5	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =-10V, V _{DS} =-15V, I _D =-5A		9.2	11	nC
Total Gate Charge (4.5V)				4.6	6	
Gate Source Charge				1.6		
Gate Drain Charge				2.2		
Turn-On DelayTime	t _{d(on)}	V _{GS} =-10V, V _{DS} =-15V, R _L =3Ω, R _{GEN} =3Ω		7.5		ns
Turn-On Rise Time	t _r			5.5		
Turn-Off DelayTime	t _{d(off)}			19		
Turn-Off Fall Time	t _f			7		
Body Diode Reverse Recovery Time	t _{rr}	I _F =-5A, di/dt=100A/μs		11		nC
Body Diode Reverse Recovery Charge	Q _{rr}			5.3		
Maximum Body-Diode Continuous Current	I _S				-2.5	A
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V			-1	V

* The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

■ Marking

Marking	D5**
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P-Channel MOSFET

AO6405 (KO6405)

■ Typical Characteristics

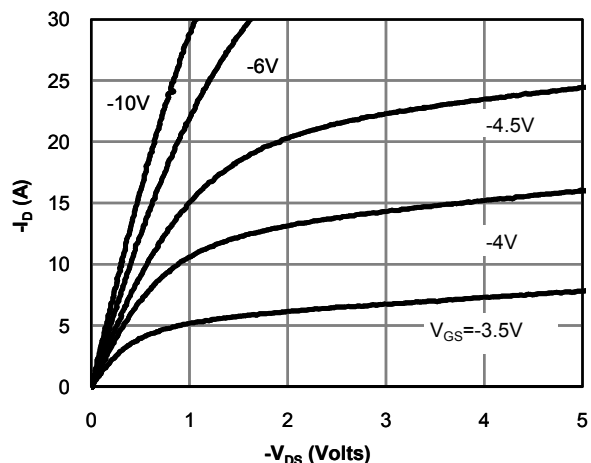


Fig 1: On-Region Characteristics (Note E)

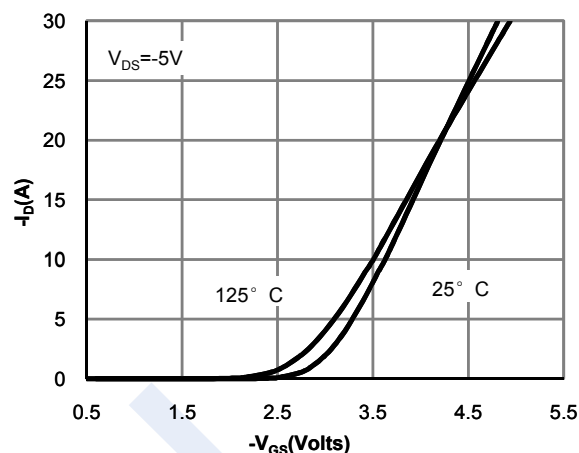


Figure 2: Transfer Characteristics (Note E)

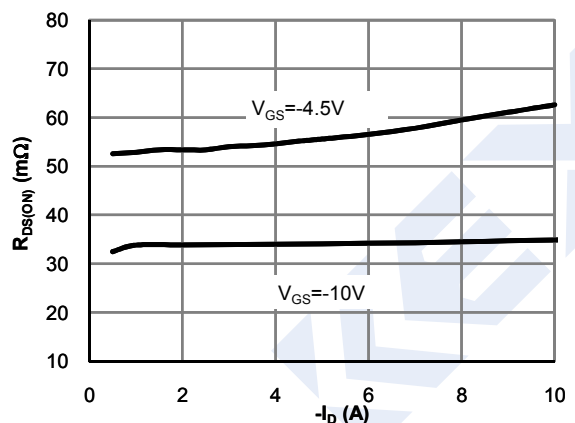


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

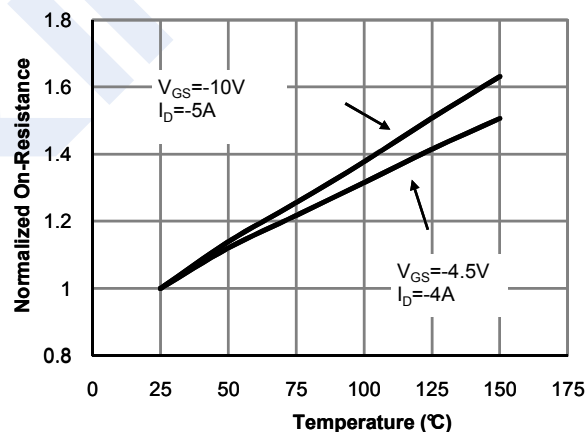


Figure 4: On-Resistance vs. Junction Temperature (Note E)

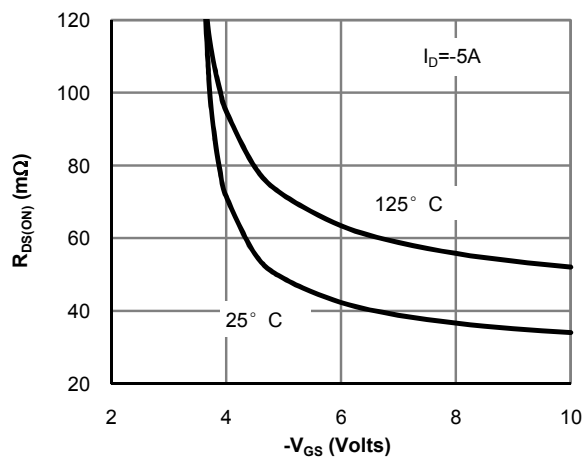


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

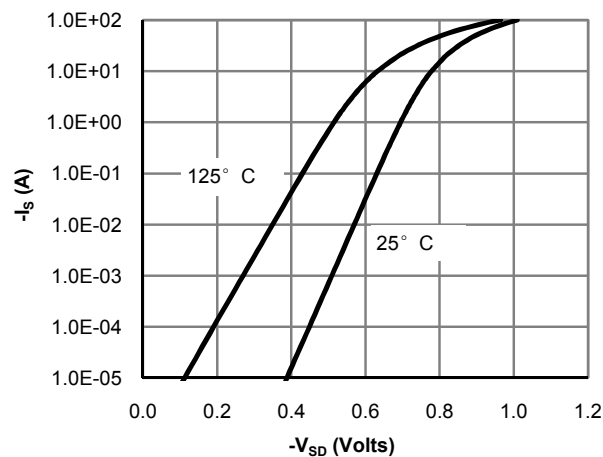


Figure 6: Body-Diode Characteristics (Note E)

P-Channel MOSFET

AO6405 (KO6405)

■ Typical Characteristics

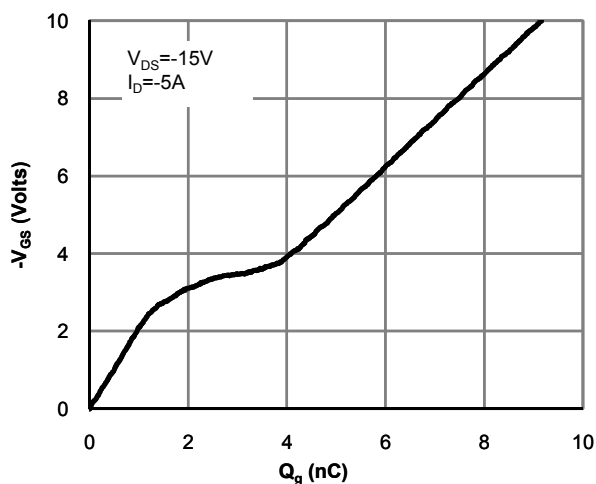


Figure 7: Gate-Charge Characteristics

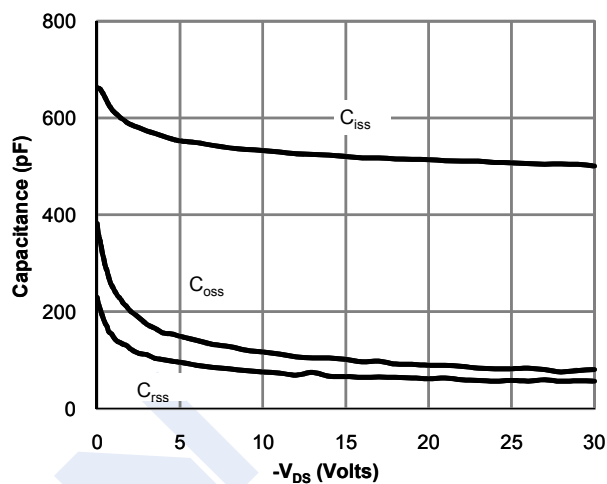


Figure 8: Capacitance Characteristics

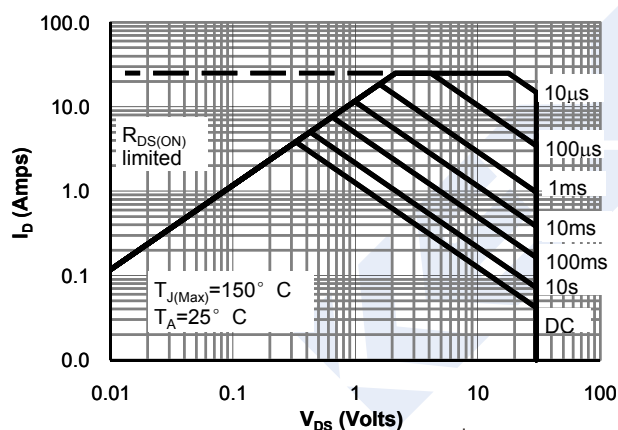


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

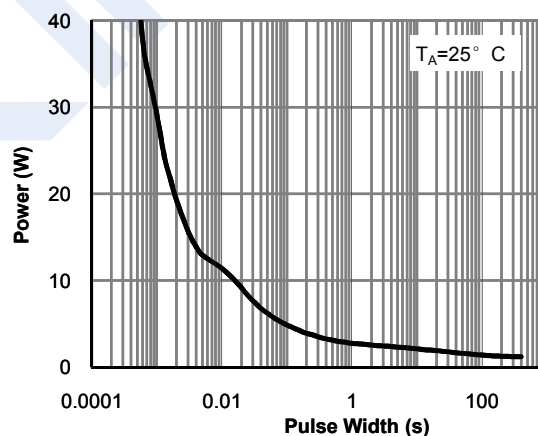


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

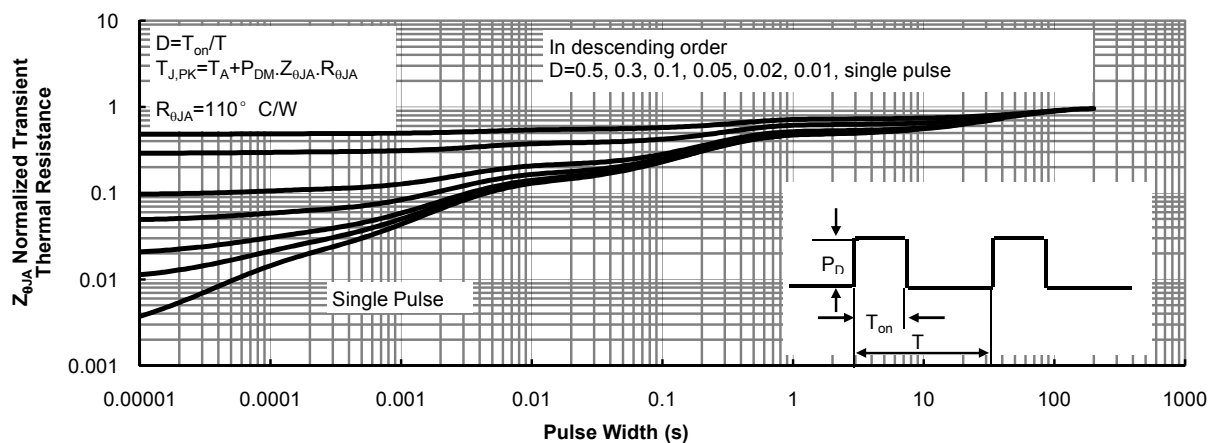


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)